

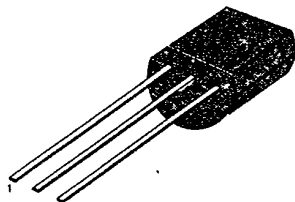
**KSC815****NPN EPITAXIAL SILICON TRANSISTOR****LOW FREQUENCY AMPLIFIER  
HIGH FREQUENCY OSCILLATOR**

- Complement to KSA539
- Collector-Base Voltage  $V_{CBO} = 60V$

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	200	mA
Collector Dissipation	$P_C$	400	mW
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 ~ 150	$^\circ C$

TO-92



1. Emitter 2. Base 3. Collector

3

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = 100\mu A, I_E = 0$	60			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = 10mA, I_B = 0$	45			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = -10\mu A, I_C = 0$	5			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 45V, I_E = 0$			0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 3V, I_C = 0$			0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 1V, I_C = 50mA$	40		400	
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = 10V, I_C = 10mA$	0.6	0.65	0.9	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150mA, I_B = 15mA$		0.15	0.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 150mA, I_B = 15mA$		0.83	1.1	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 10mA$	100	200		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0$ $f = 1MHz$		4		pF

 **$h_{FE}$  CLASSIFICATION**

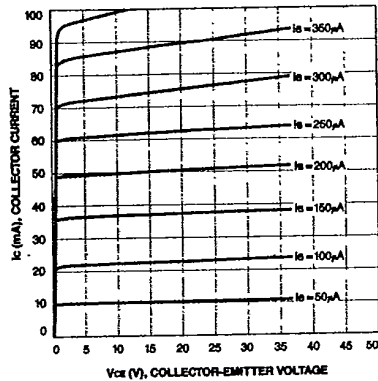
Classification	R	O	Y	G
$h_{FE}$	40-80	70-140	120-240	200-400



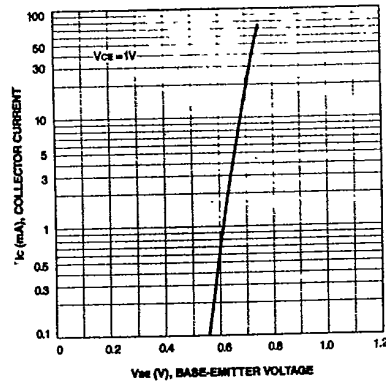
KSC815

NPN EPITAXIAL SILICON TRANSISTOR

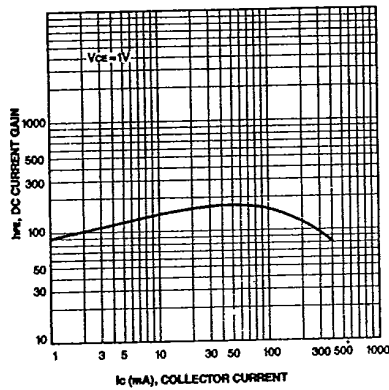
STATIC CHARACTERISTIC



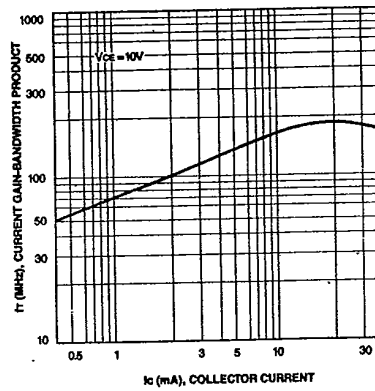
BASE-EMITTER ON VOLTAGE



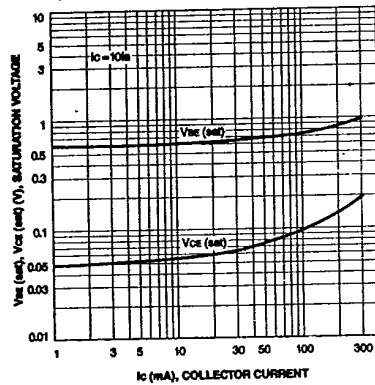
DC CURRENT GAIN



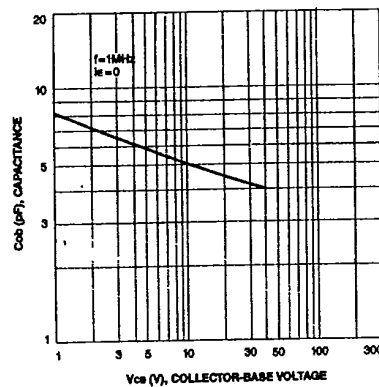
CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE  
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



SAMSUNG SEMICONDUCTOR